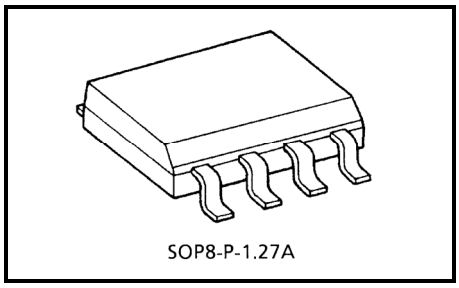
TOSHIBA Intelligent Power Device Silicon Monolithic Power MOS Integrated Circuit

TPD1034F

High-side Power Switch for Motors, Solenoids, and Lamp Drivers

The TPD1034F is a monolithic power IC for high-side switches. The IC has a vertical MOS FET output which can be directly driven from a CMOS or TTL logic circuit (e.g., an MPU). The device offers intelligent self-protection and diagnostic functions.



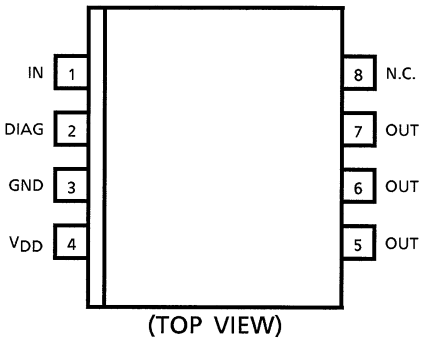
Weight: 0.08 g (typ.)

Features

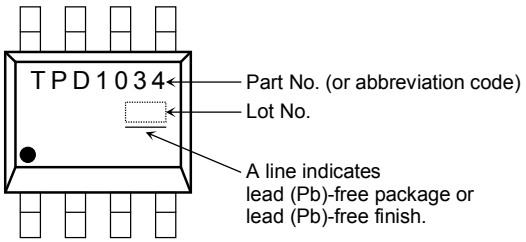
- A monolithic power IC with a new structure combining a control block (Bi-CMOS) and a vertical power MOS FET (π-MOS) on a single chip.
- One side of the load can be grounded to a high-side switch.
- Can directly drive a power load from a microprocessor.
- Built-in protection against thermal shutdown and load short-circuiting.
- Incorporates a diagnosis function that allows diagnosis output to be read externally at load short-circuiting, opening, or overtemperature
- Up to −10 V of counter electromotive force from an L load can be applied.
- Low on-resistance : R_{ON} = 80 mΩ (max)
- Low operating current : I_{DD} = 1 mA (typ.), (@V_{DD} = 12 V, V_{IN} = 0 V)
- 8-pin SOP package for surface mounting can be packed in tape.

Note: Due to its MOS structure, this product is sensitive to static electricity. Handle with care.

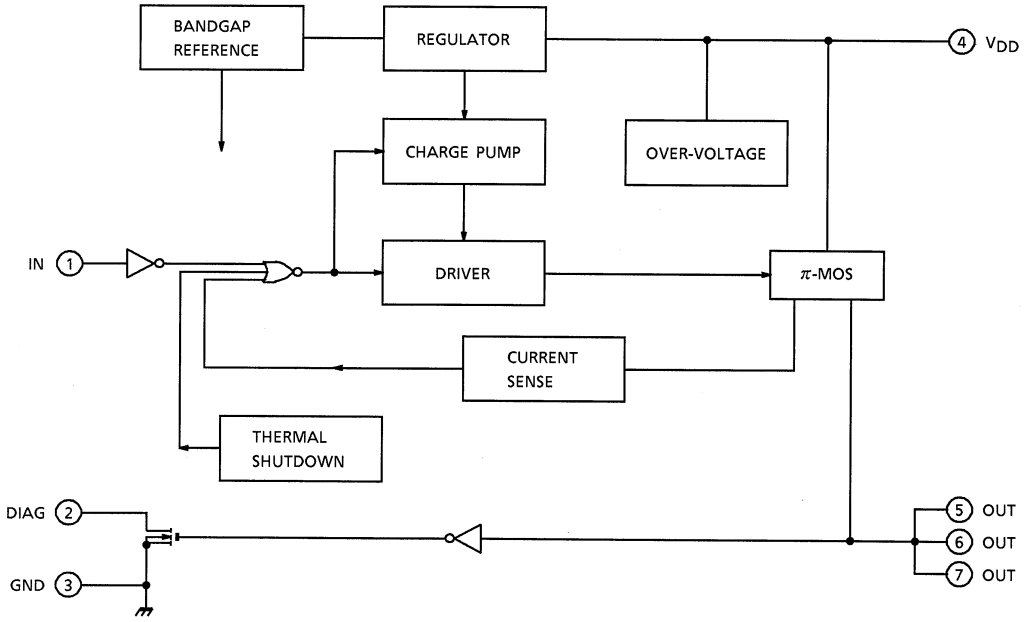
Pin Assignment



Marking



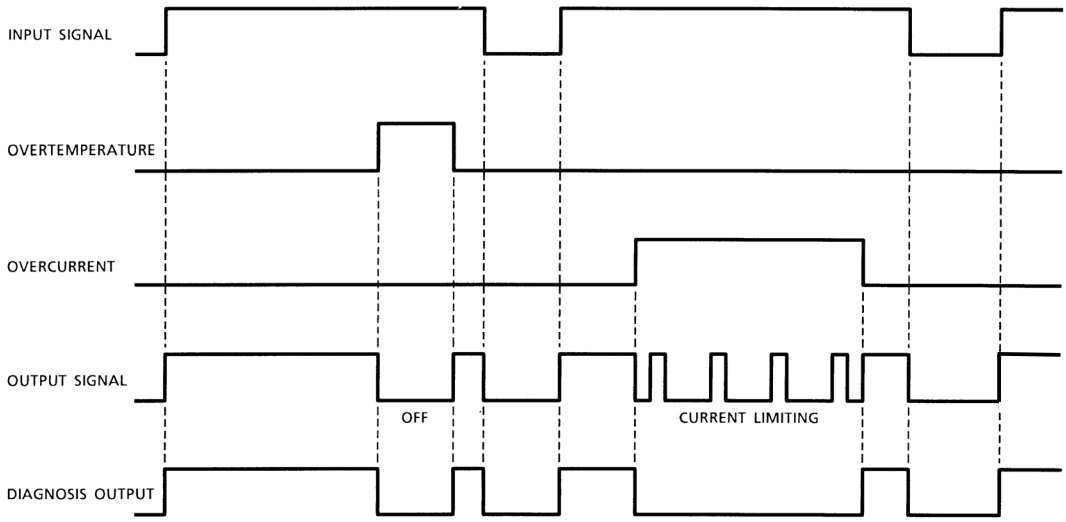
Block Diagram



Pin Description

Pin No.	Symbol	Function
1	IN	Input pin. Input is CMOS-compatible, with pull-down resistor connected. Even if the input is open, output will not accidentally turn on.
2	DIAG	Self-diagnosis detection pin. Goes low when overheating is detected or when output is short-circuited with input on (high). n-channel open drain.
3	GND	Ground pin.
4	V_{DD}	Power pin.
5, 6, 7	OUT	Output pin. When the load is short circuited and current in excess of the detection current (24A typ.) flows to the output pin, the output automatically turns on or off.

Timing Chart



Truth Table

Input Signal	Output Signal	Diagnosis Output	State
H	H	H	Normal
L	L	L	
H	L	L	Overcurrent
L	L	L	
H	H	H	Load open
L	H	H	
H	L	L	Overtemperature
L	L	L	

Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unite
Drain-source voltage		V_{DS}	60	V
Supply voltage	DC	$V_{DD\ (1)}$	25	V
	Pulse	$V_{DD\ (2)}$	60 (Rs = 1Ω, τ= 250 ms)	V
Input voltage	DC	$V_{IN\ (1)}$	−0.5 ~ 12	V
	Pulse	$V_{IN\ (2)}$	$V_{DD\ (1)}$ + 1.5 (t = 100 ms)	V
Diagnosis output voltage		V_{DIAG}	−0.5 ~ 25	V
Output current		I_O	Internally limited	A
Input current		I_{IN}	±10	mA
Diagnosis output current		I_{DIAG}	5	mA
Power dissipation (Ta = 25°C)		P_D	1.4 (Note 1)	W
			2.4 (Note 2)	
Operating temperature		T_{opr}	−40 ~ 110	°C
Channel temperature		T_{ch}	150	°C
Storage temperature		T_{stg}	−55 ~ 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Resistance

Characteristic	Symbol	Test Condition	Unit
Thermal resistance	$R_{th\ (ch-a)}$	89.3 (Note 1)	°C / W
		52.1 (Note 2)	

Note1: Mounted on a glass epoxy board (25.4 mm × 25.4 mm × 0.8 mm) (DC)
Note2: Mounted on a glass epoxy board (25.4 mm × 25.4 mm × 0.8 mm) ($t_W \leq 10$ s)

Electrical Characteristics

(Unless otherwise specified, T_{ch} = − 40 ~ 110°C, V_{DD} = 8 ~ 18 V)

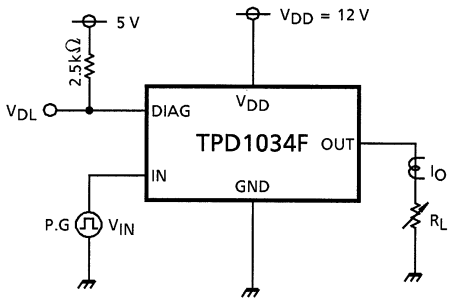
Characteristic		Symbol	Test Cir-cuit	Test Condition	Min	Typ.	Max	Unit
Operating supply voltage		$V_{DD\ (opr)}$	—	—	5	12	18	V
Supply current		I_{DD}	—	V_{DD} = 12 V, V_{IN} = 0	—	1	5	mA
Input voltage		V_{IH}	—	V_{DD} = 12 V, I_O = 8 A	3.5	—	—	V
		V_{IL}	—	V_{DD} = 12 V, I_O = 1.2 mA	—	—	1.5	V
Input current		$I_{IN\ (1)}$	—	V_{DD} = 12 V, V_{IN} = 5 V	—	50	200	μA
		$I_{IN\ (2)}$	—	V_{DD} = 12 V, V_{IN} = 0	−0.2	—	0.2	μA
On-voltage		$V_{DS\ (ON)}$	—	V_{DD} = 12 V, I_O = 8 A, T_{ch} = 25°C	—	—	0.64	V
On-resistance		$R_{DS\ (ON)}$	—	V_{DD} = 12 V, I_O = 8 A, T_{ch} = 25°C	—	—	0.08	Ω
Output leakage current		I_{OL}	—	V_{DD} = 18 V, V_{IN} = 0	—	—	1.2	mA
Diagnosis output voltage	“L” Level	V_{DL}	—	V_{DD}=12 V, I_{DL} = 2 mA	—	—	0.4	V
Diagnosis output current	“H” Level	I_{DH}	—	V_{DD} = 18 V, V_{DH} = 18 V	—	—	10	μA
Overcurrent protection		$I_{S\ (1)}$ Note 3	1	V_{DD} = 12 V, T_{ch} = 25°C	8	12	—	A
		$I_{S\ (2)}$ Note 4	2		15	24	—	A
Thermal shutdown	Temperature	Ts	—	—	150	160	200	°C
	Hysteresis	ΔTs	—		—	10	—	°C
Open detection resistance		R_{ops}	—	V_{DD} = 8 V	1	50	100	kΩ
Switching time		t_{ON}	3	V_{DD} = 12 V, R_L = 5Ω, T_{ch} = 25°C	10	200	—	μs
		t_{OFF}	3		10	30	—	μs

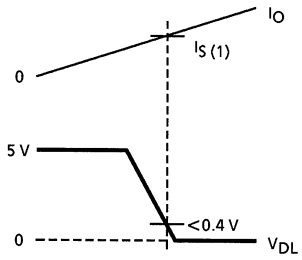
Note 3: $I_{S\ (1)}$ denotes the overcurrent detection value when the load is short circuited and V_{IN} = “L” → “H”

Note 4: $I_{S\ (2)}$ denotes the overcurrent detection value when the load current is increased while V_{IN} = “H”

Test Circuit 1

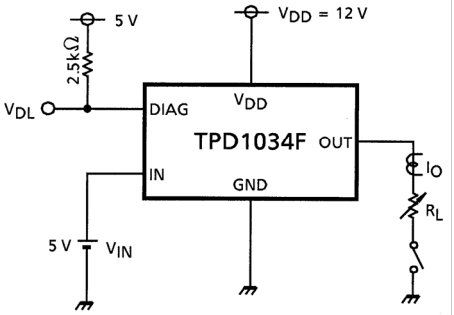
Overcurrent detection

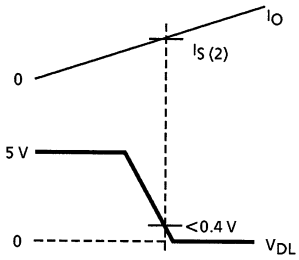




Test Circuit 2

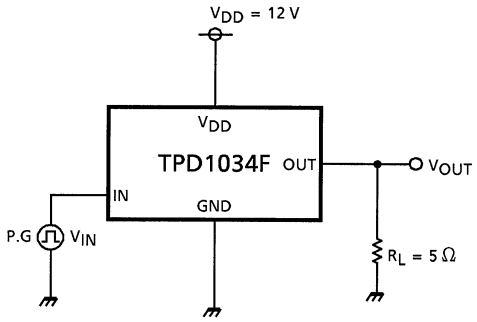
Overcurrent detection

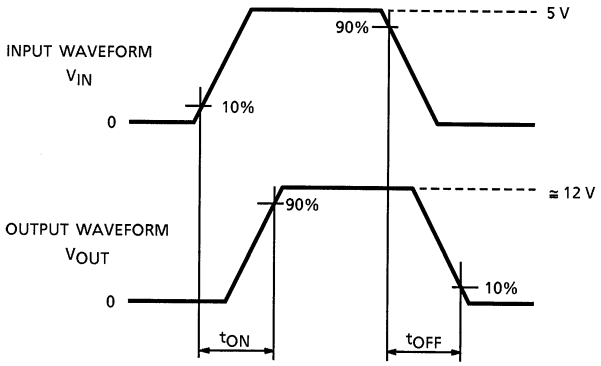




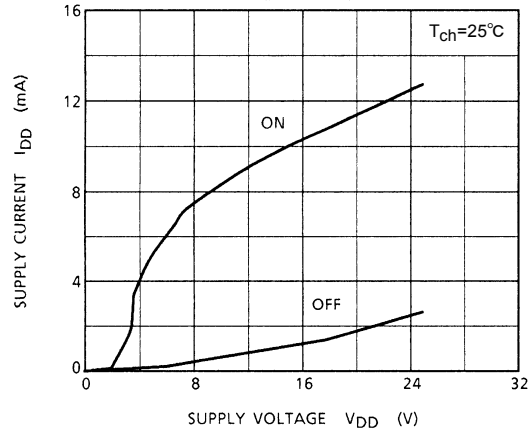
Test Circuit 3

Switching time

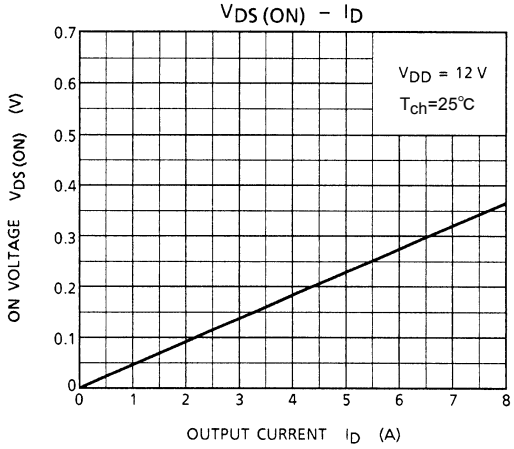




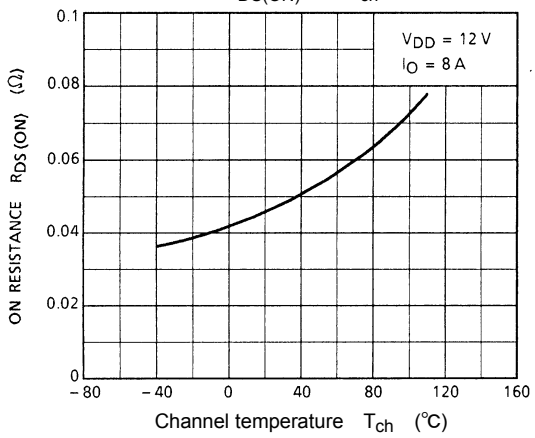
I_{DD} – V_{DD}



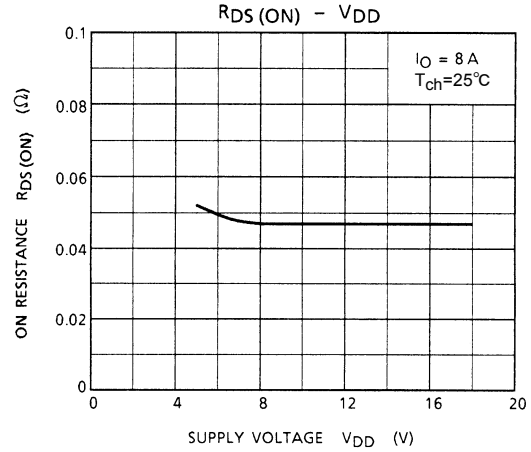
$V_{DS\ (ON)}$ – I_D



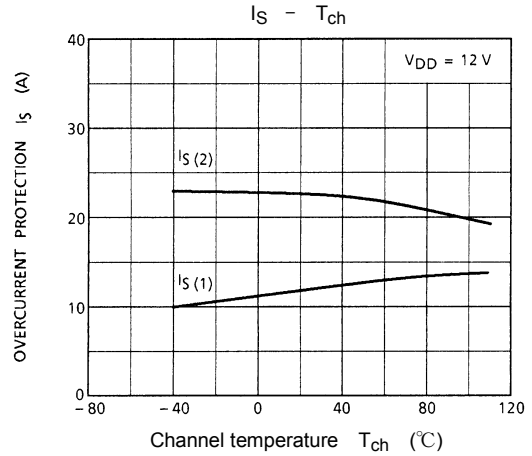
$R_{DS(ON)}$ – T_{ch}



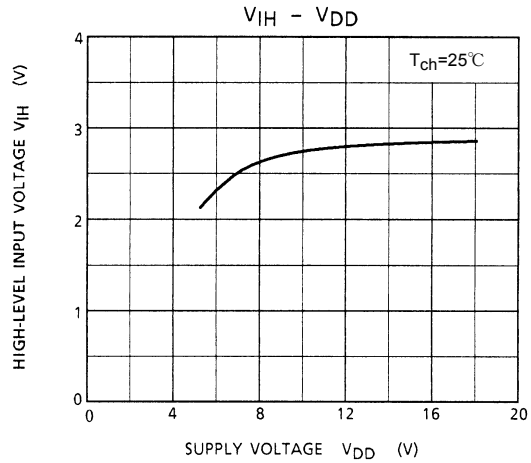
$R_{DS\ (ON)}$ – V_{DD}

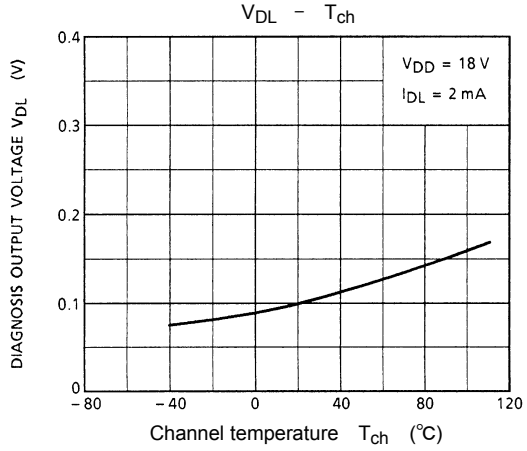


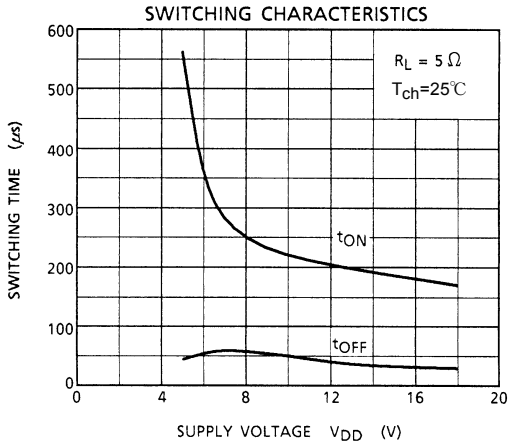
I_S – T_{ch}

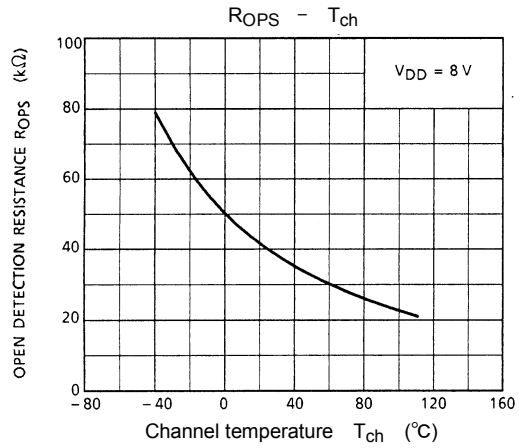


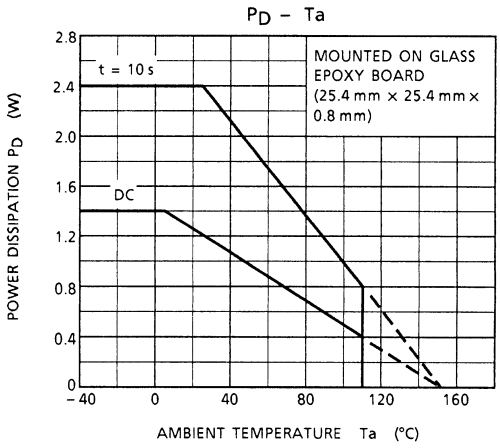
V_{IH} – V_{DD}

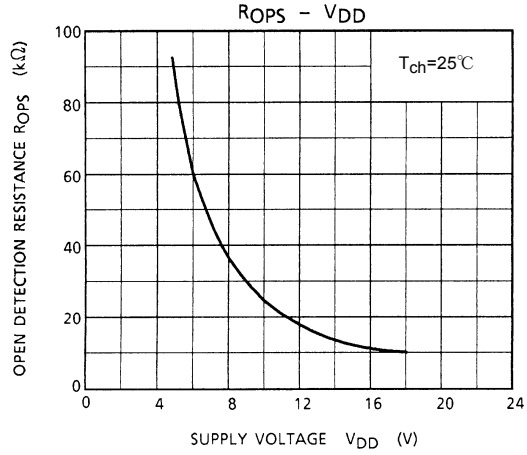












Precaution:

1. Since there is no built-in protection against reverse connection of batteries, etc., provide such protection using external circuits.

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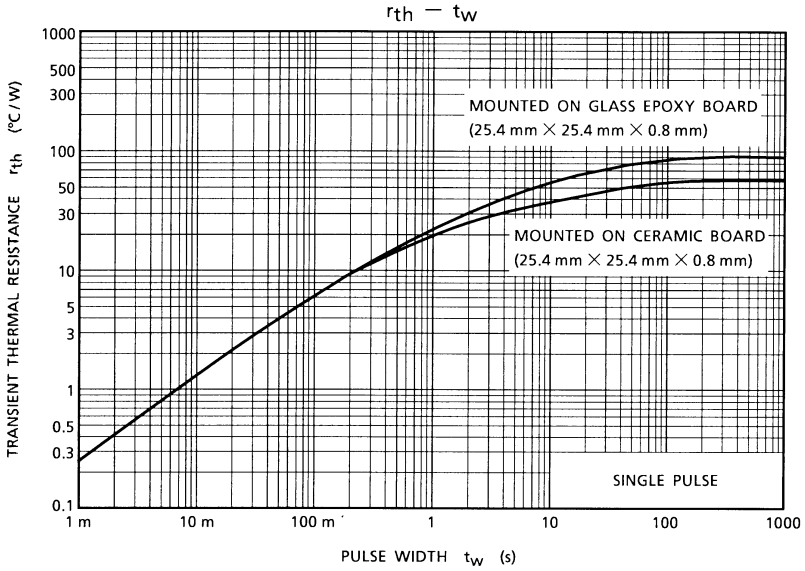
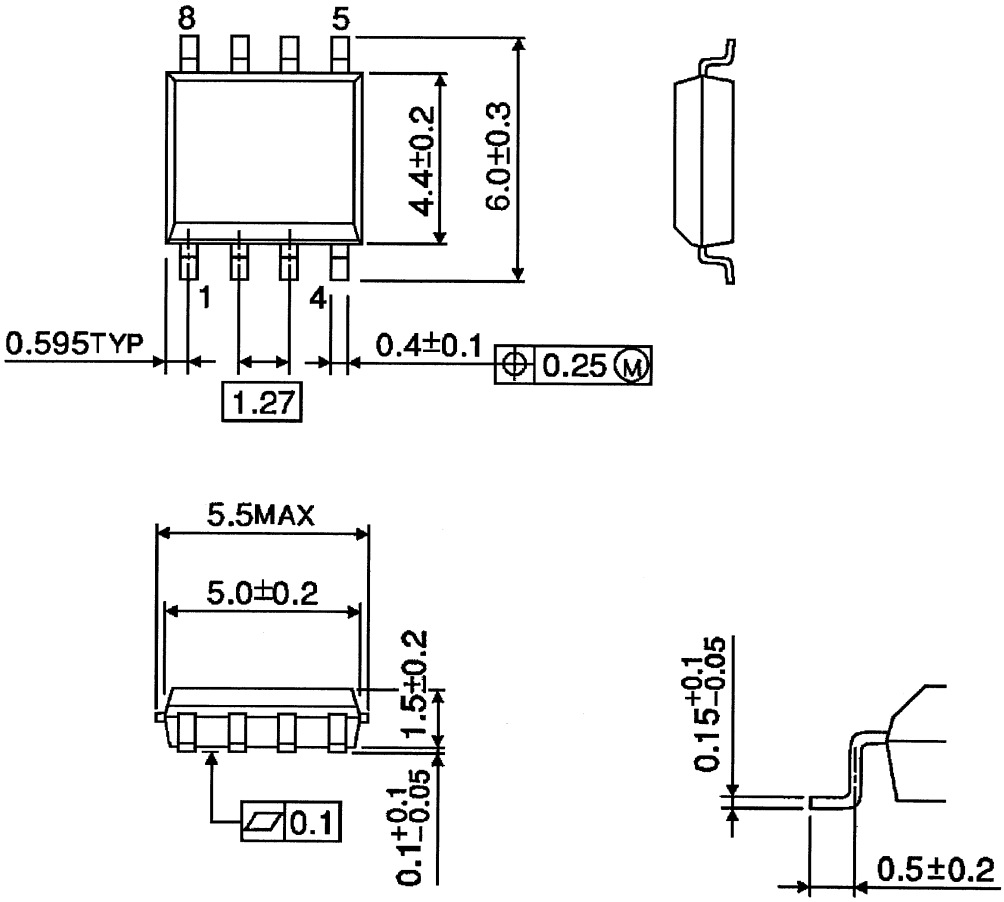

r_{th} – t_W
TRANSIENT THERMAL RESISTANCE r_{th} (°C/W)
1000
500
300
100
50
30
10
5
3
1
0.5
0.3
0.1
MOUNTED ON GLASS EPOXY BOARD
(25.4 mm × 25.4 mm × 0.8 mm)
MOUNTED ON CERAMIC BOARD
(25.4 mm × 25.4 mm × 0.8 mm)
SINGLE PULSE
1 m
10 m
100 m
1
10
100
1000
PULSE WIDTH t_W (s)

Package Dimensions

SOP8-P1.27A

Unit : mm



Weight: 0.08 g (typ.)

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